

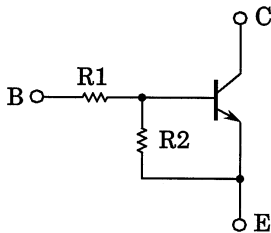
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

## RN1101MFV, RN1102MFV, RN1103MFV RN1104MFV, RN1105MFV, RN1106MFV

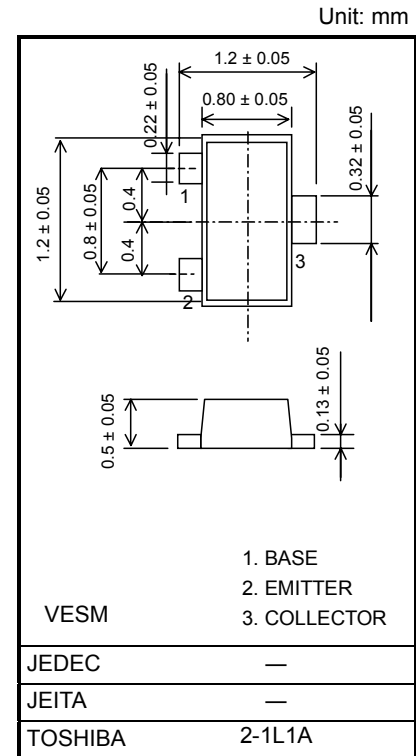
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Ultra-small package, suited to very high density mounting
- Incorporating a bias resistor into the transistor reduces the number of parts, so enabling the manufacture of ever more compact equipment and lowering assembly cost.
- A wide range of resistor values is available for use in various circuits.
- Complementary to the RN2101MFV~RN2106MFV
- Lead (Pb) - free

### Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN1101MFV	4.7	4.7
RN1102MFV	10	10
RN1103MFV	22	22
RN1104MFV	47	47
RN1105MFV	2.2	47
RN1106MFV	4.7	47

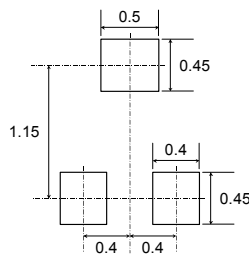


Weight: 0.0015 g (typ.)

### Maximum Ratings (Ta = 25°C)

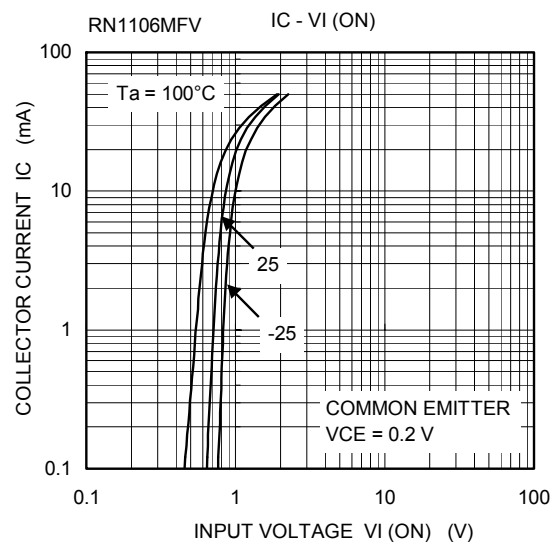
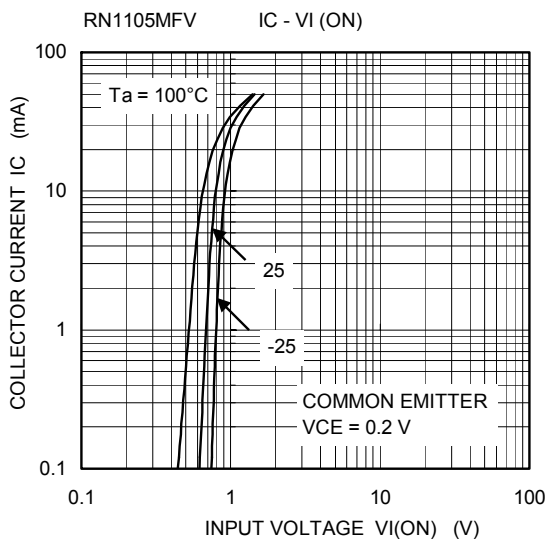
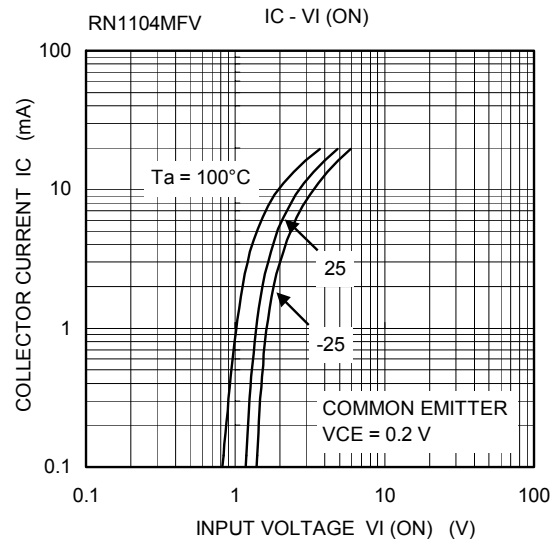
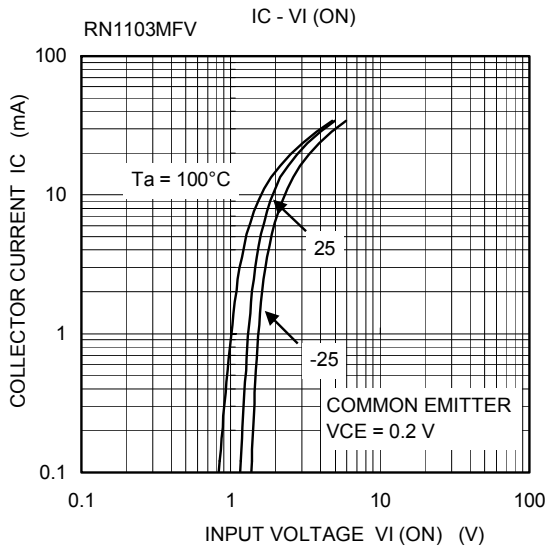
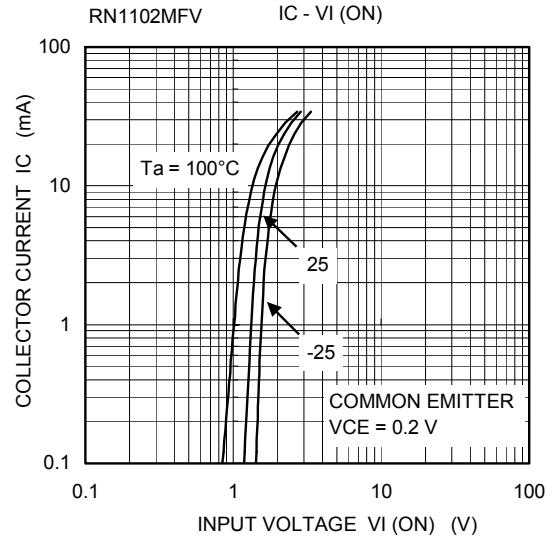
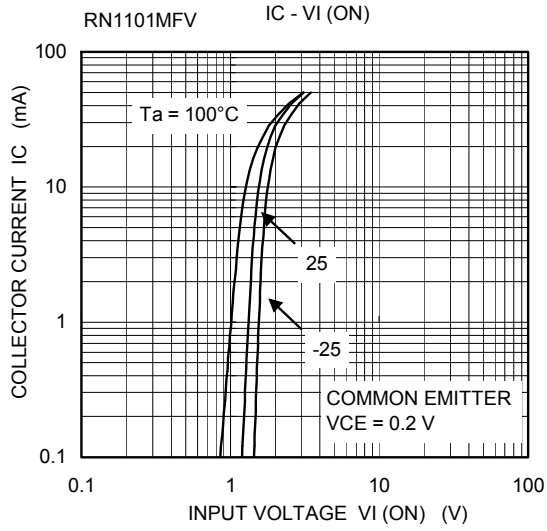
Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN1101MFV~1106MFV	$V_{CBO}$	50	V
Collector-emitter voltage		$V_{CEO}$	50	V
Emitter-base voltage	RN1101MFV~1104MFV	$V_{EBO}$	10	V
	RN1105MFV, 1106MFV		5	
Collector current	RN1101MFV~1106MFV	$I_C$	100	mA
Collector power dissipation		$P_C$ (Note)	150	mW
Junction temperature		$T_j$	150	°C
Storage temperature range		$T_{stg}$	-55~150	°C

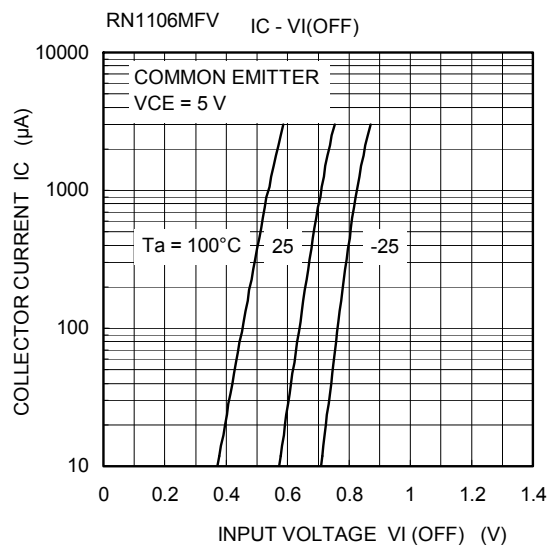
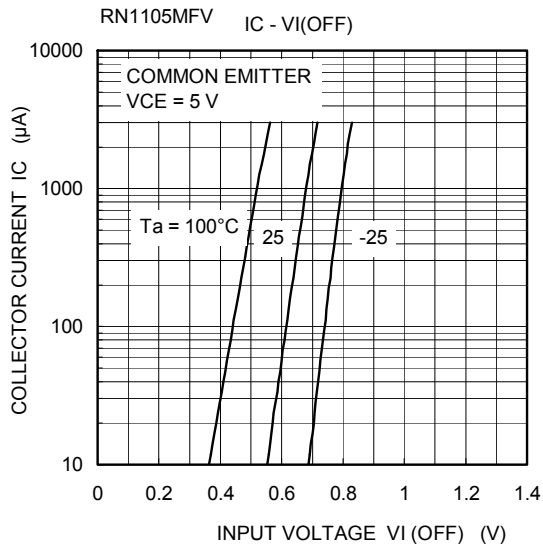
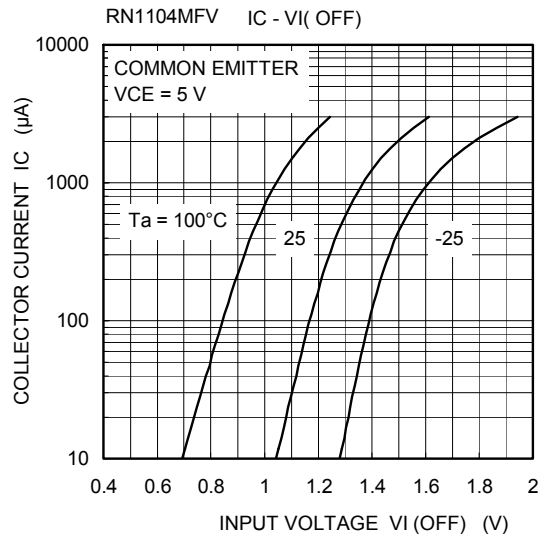
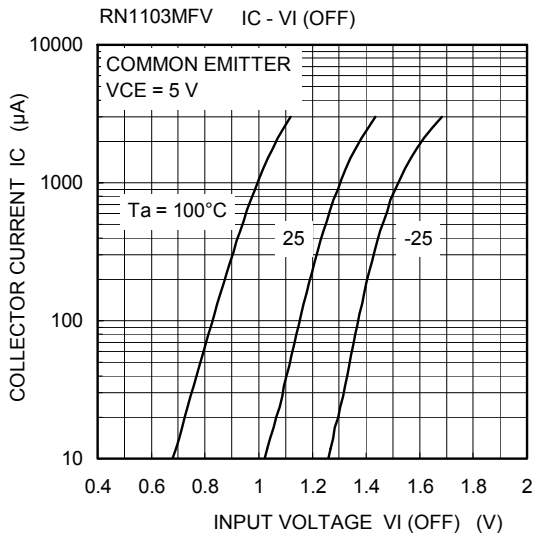
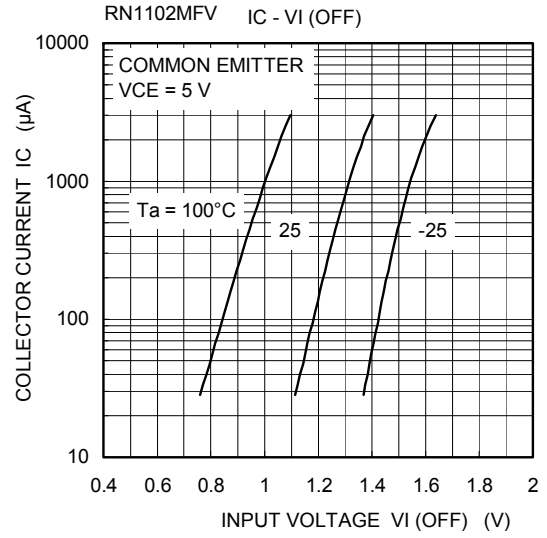
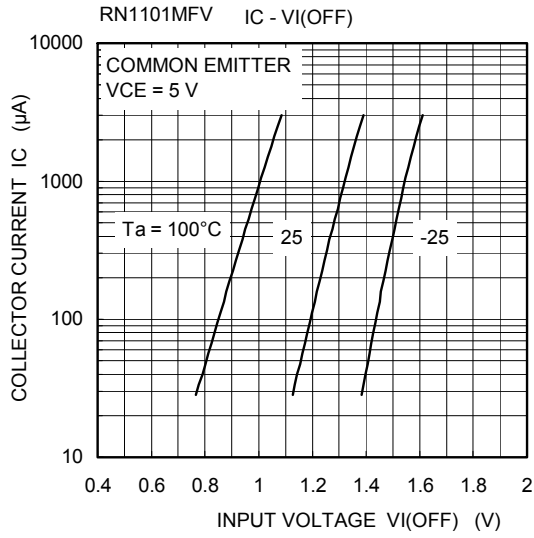
Note: Mounted on an FR4 board (25.4 mm × 25.4 mm × 1.6 mm)

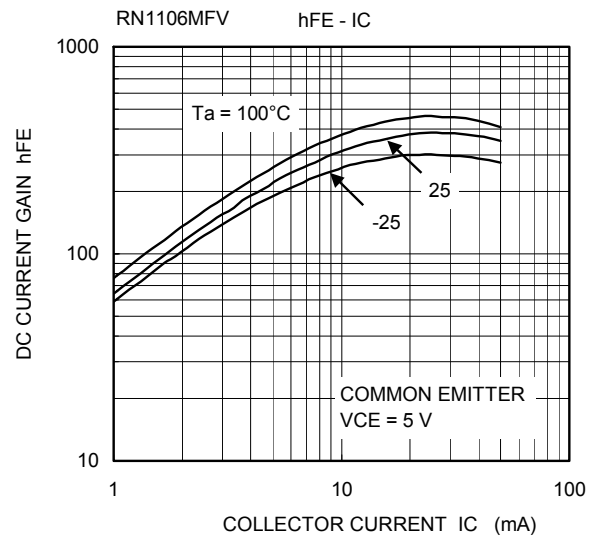
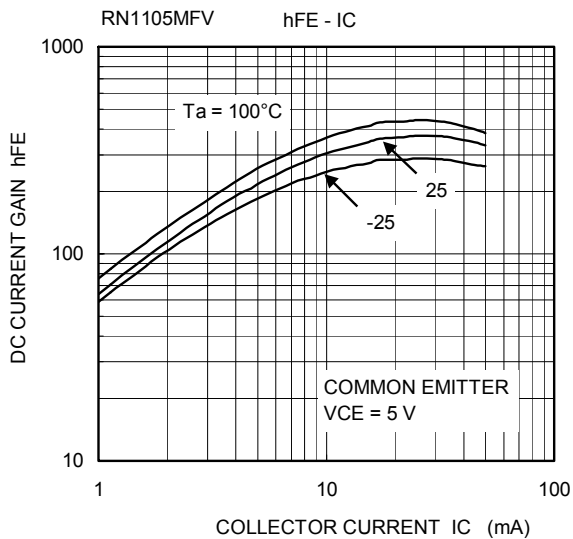
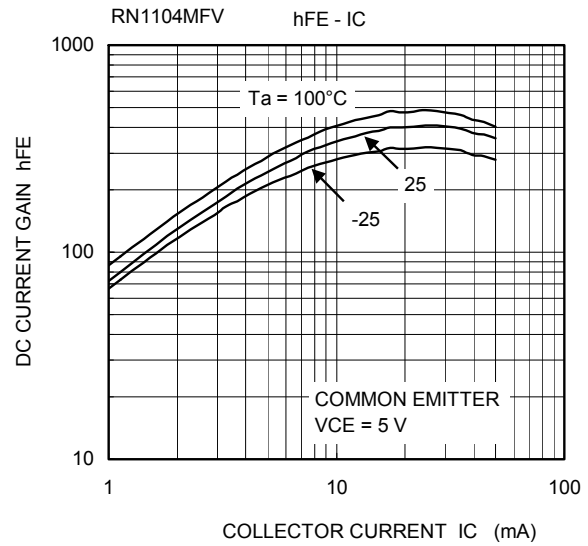
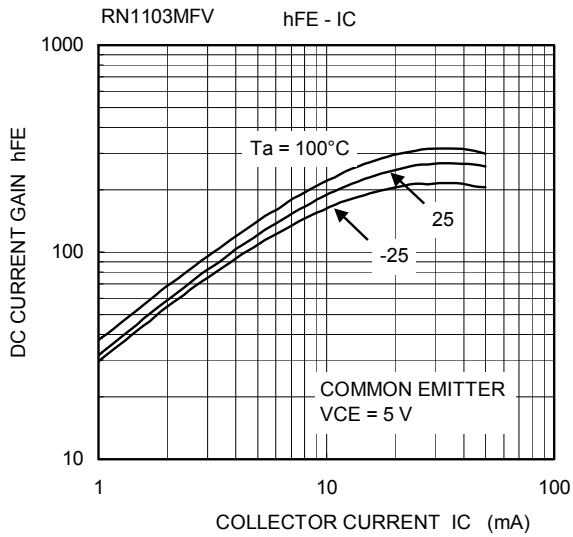
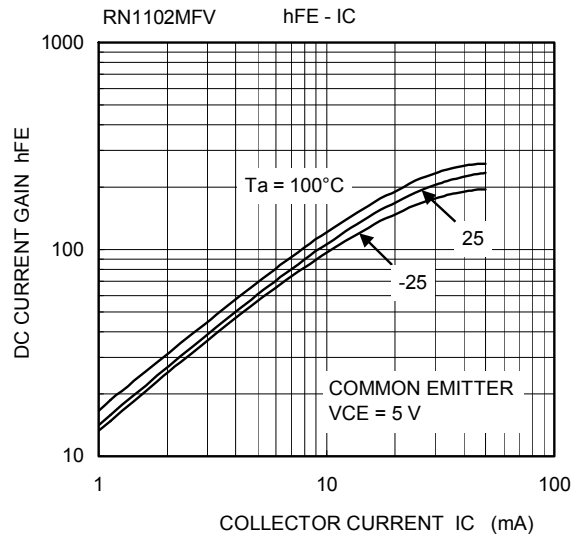
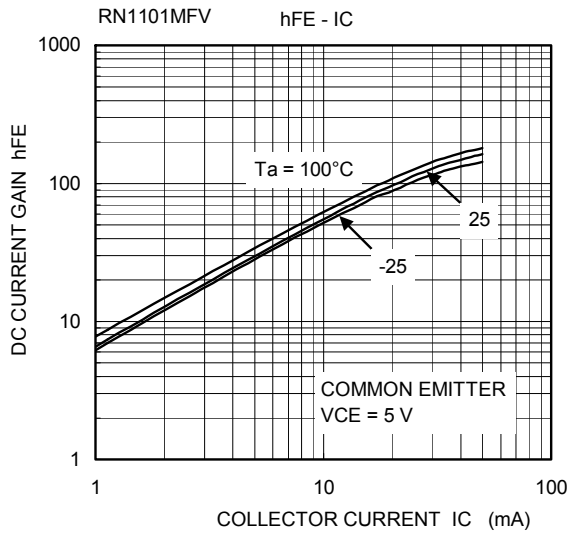


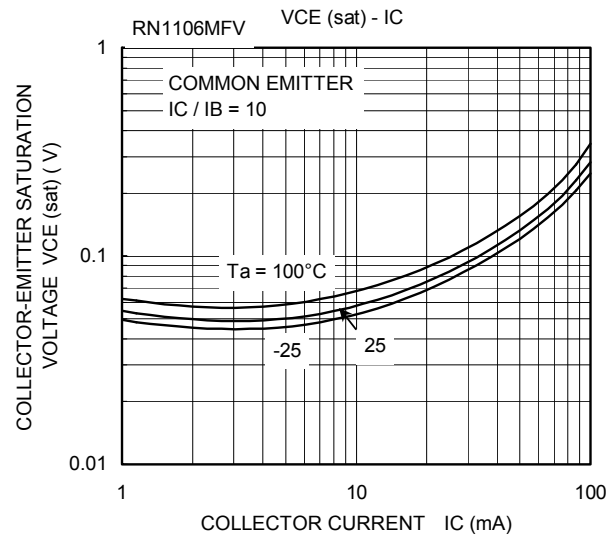
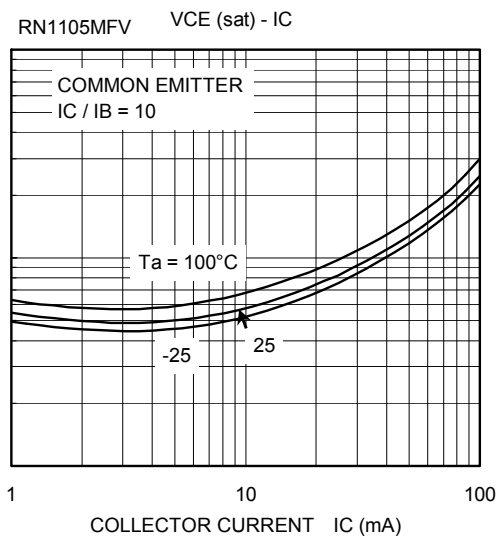
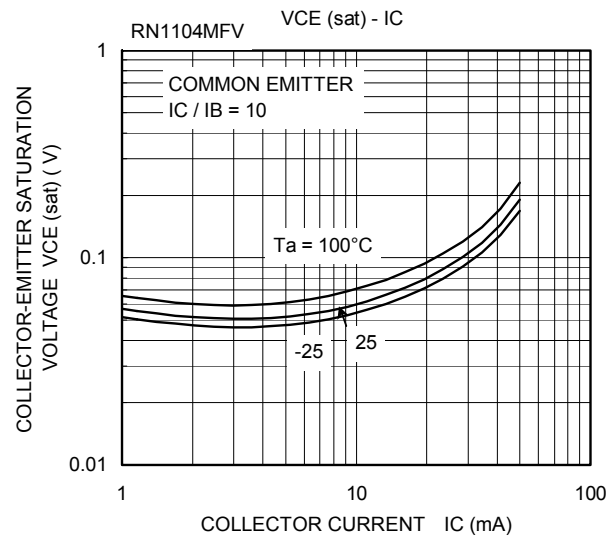
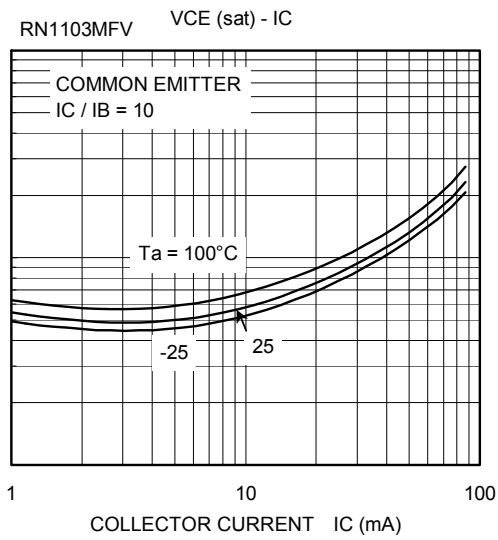
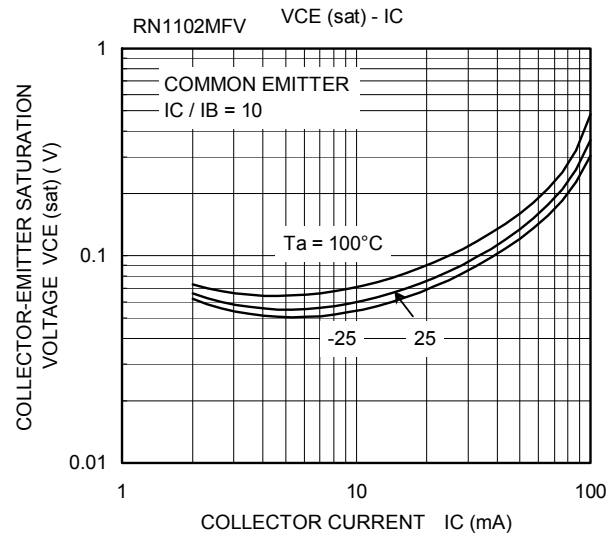
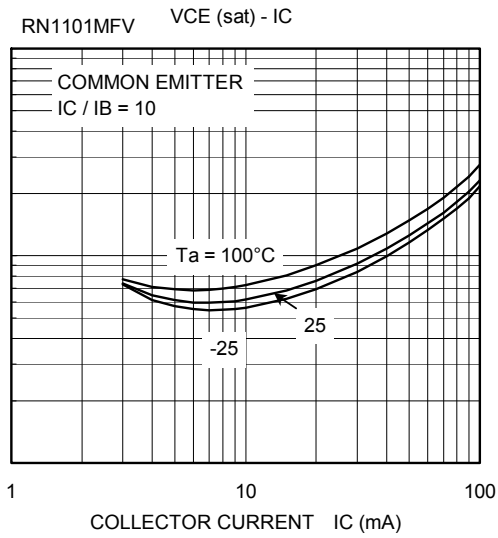
**Electrical Characteristics (Ta = 25°C)**

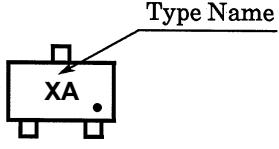
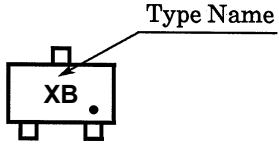
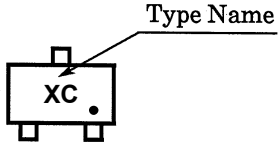
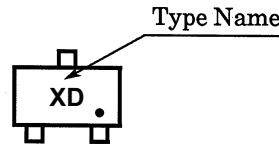
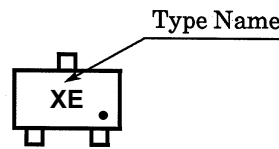
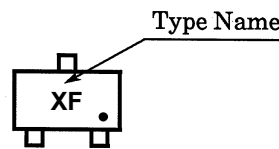
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	RN1101MFV~1106MFV	$I_{CBO}$	—	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	100	nA
		$I_{CEO}$	—	$V_{CE} = 50\text{ V}, I_B = 0$	—	—	500	
Emitter cutoff current	RN1101MFV	$I_{EBO}$	—	$V_{EB} = 10\text{ V}, I_C = 0$	0.82	—	1.52	mA
	RN1102MFV				0.38	—	0.71	
	RN1103MFV				0.17	—	0.33	
	RN1104MFV				0.082	—	0.15	
	RN1105MFV			$V_{EB} = 5\text{ V}, I_C = 0$	0.078	—	0.145	
	RN1106MFV				0.074	—	0.138	
DC current gain	RN1101MFV	$h_{FE}$	—	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	30	—	—	
	RN1102MFV				50	—	—	
	RN1103MFV				70	—	—	
	RN1104MFV				80	—	—	
	RN1105MFV				80	—	—	
	RN1106MFV				80	—	—	
Collector-emitter saturation voltage	RN1101MFV~1106MFV	$V_{CE(sat)}$	—	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	0.1	0.3	V
Input voltage (ON)	RN1101MFV	$V_{I(ON)}$	—	$V_{CE} = 0.2\text{ V}, I_C = 5\text{ mA}$	1.1	—	2.0	V
	RN1102MFV				1.2	—	2.4	
	RN1103MFV				1.3	—	3.0	
	RN1104MFV				1.5	—	5.0	
	RN1105MFV				0.6	—	1.1	
	RN1106MFV				0.7	—	1.3	
Input voltage (OFF)	RN1101MFV~1104MFV	$V_{I(OFF)}$	—	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ mA}$	1.0	—	1.5	V
	RN1105MFV, 1106MFV				0.5	—	0.8	
Collector output capacitance	RN1101MFV~1106MFV	$C_{ob}$	—	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.7	—	pF
Input resistor	RN1101MFV	R1	—	—	3.29	4.7	6.11	kΩ
	RN1102MFV				7	10	13	
	RN1103MFV				15.4	22	28.6	
	RN1104MFV				32.9	47	61.1	
	RN1105MFV				1.54	2.2	2.86	
	RN1106MFV				3.29	4.7	6.11	
Resistor ratio	RN1101MFV~1104MFV	R1/R2	—	—	0.8	1.0	1.2	
	RN1105MFV				0.0376	0.0468	0.0562	
	RN1106MFV				0.08	0.1	0.12	









Type Name	Marking
RN1101MFV	
RN1102MFV	
RN1103MFV	
RN1104MFV	
RN1105MFV	
RN1106MFV	

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